



30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

42 A

Features

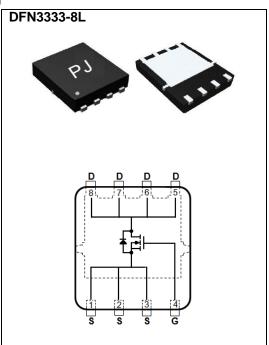
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@16A<9m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@8A<13m\Omega$
- · High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAME	TER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Ocaliana Paris Ocares	T _C =25°C	I _D	42		
Continuous Drain Current	T _C =100°C		26	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	168		
Power Dissipation	T _C =25°C	Po	35	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
	T _C =100°C		14	W	
Continuous Drain Current	T _A =25°C	I _D	10	А	
	T _A =70°C		8		
Power Dissipation	T _A =25°C	1	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
(Note 4.5)	Junction to Case	$R_{ heta JC}$	3.6	°C/W	
Typical Thermal Resistance ^(Note 4,5)	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS(th)}$ $V_{DS}=V_{GS},I_D=250uA$		1.7	2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =16A	-	6.2	9	mΩ	
Drain-Source On-State Resistance		V _{GS} =4.5V,I _D =8A	-	9.6	13		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1.0	uA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Q_g	V _{DS} =15V, I _D =20A, V _{GS} =4.5V ^(Note 2,3)	-	7.1	-	nC	
Gate-Source Charge	Q_gs		-	3.1	-		
Gate-Drain Charge	Q_{gd}		-	2.0	-		
Input Capacitance	Ciss	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	-	763	-	pF	
Output Capacitance	Coss	V_{DS} =25V, V_{GS} =0V, f=1.0MHZ	-	132	-		
Reverse Transfer Capacitance	Crss	I=1.UIVITZ	-	81	-		
Turn-On Delay Time	td _(on)	V_{DS} =15V, I_{D} =15A,	-	5.4	-		
Turn-On Rise Time	t _r	V_{GS} =10V, R_{G} =6 Ω	-	86	-	ns	
Turn-Off Delay Time	td _(off)	(Note 2,3)	-	20	-		
Turn-Off Fall Time	t _f		-	10	-		
Drain-Source Diode			_				
Maximum Continuous Drain-Source	ı				42	Α	
Diode Forward Current	I _S		_		44	_ ^	
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	_	0.7	1.0	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

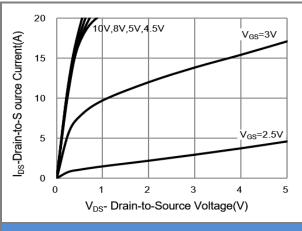


Fig.1 On-Region Characteristics

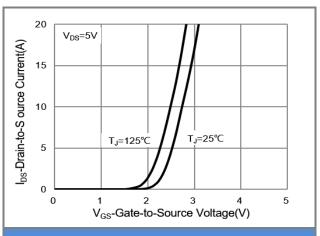


Fig.2 Transfer Characteristics

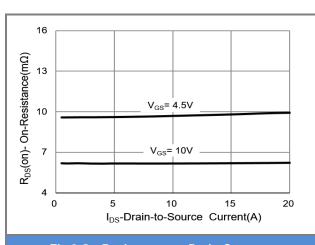


Fig.3 On-Resistance vs. Drain Current

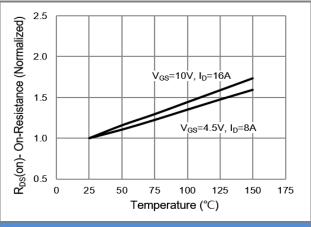


Fig.4 On-Resistance vs. Junction temperature

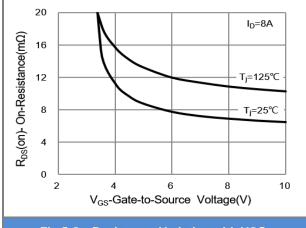


Fig.5 On-Resistance Variation with VGS.

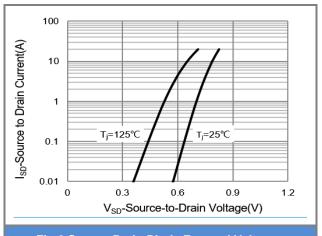


Fig.6 Source-Drain Diode Forward Voltage





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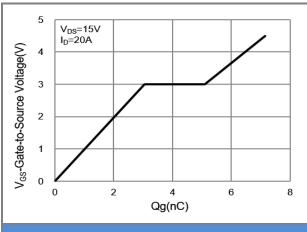


Fig.7 Gate-Charge Characteristics

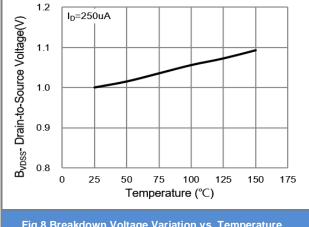


Fig.8 Breakdown Voltage Variation vs. Temperature.

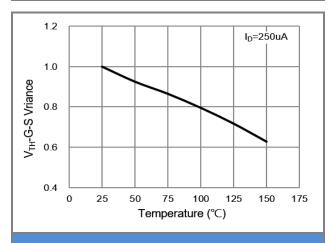


Fig.9 Threshold Voltage Variation with Temperature

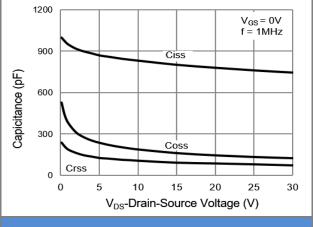


Fig.10 Capacitance vs. Drain-Source Voltage.

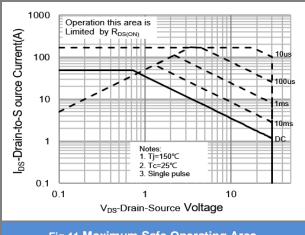


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

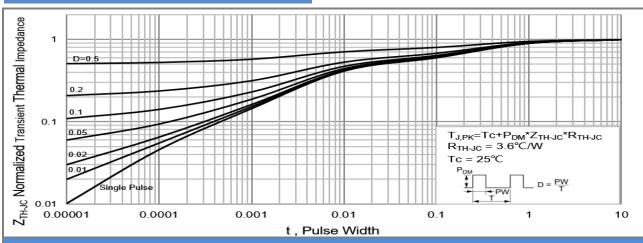


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

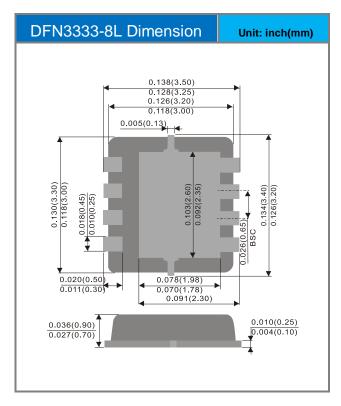


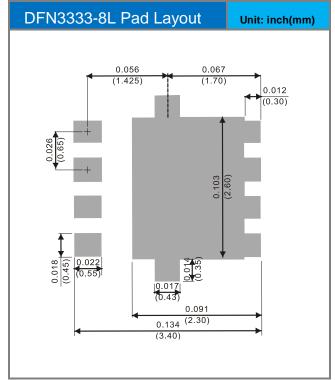


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ4408P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4408	Halogen free	

Packaging Information & Mounting Pad Layout









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